

EPIC Online Technology Meeting on Lithography

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Strategic Business Development (Corporate Strategy & Marketing)

3rd July 2020

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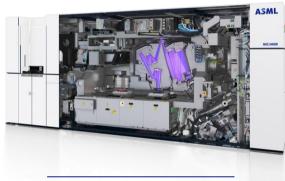
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Lithography systems for multiple markets Our customers range from <7nm logic fabs to III-V photonic fabs



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EUV

TWINSCAN NXE:3400C

Wavelength: 13.5 nm **Resolution:** 13 nm NA: 0.33 Overlay: 1.0 nm Wafer size: 300 mm **Productivity:** 170 wph

In the same way that 0.33NA enables 7nm and 5nm Logic, 0.55NA EUV will be needed to enable 3nm Logic



Immersion

TWINSCAN NXT:2000i

Wavelength: 193 nm Resolution: ≤ 38 nm NA: 1.35 Overlay: ~1.5 nm Wafer size: 300 mm Productivity: 275 wph

State-of-the-art immersion systems, in high-volume manufacturing of the 7nm Logic and advanced DRAM nodes



Mature Products

Steppers & Scanners

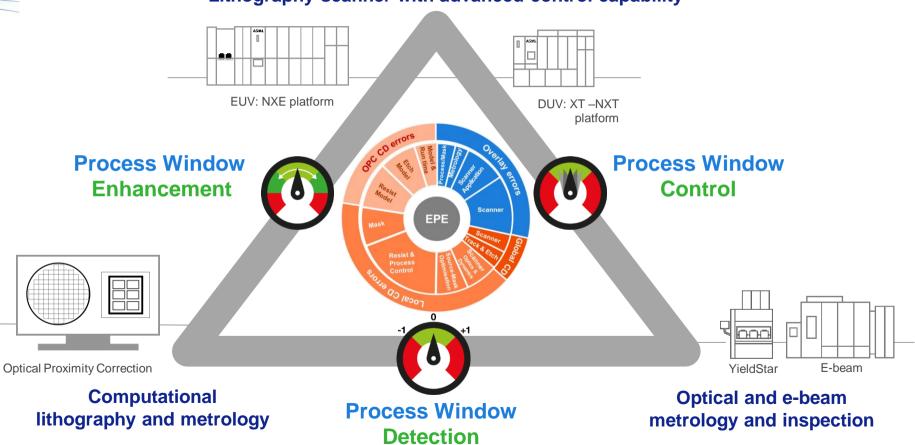
Wavelength: 365 to 193 nm Resolution: Overlay: Wafer size: Productivity:

400 to 90 nm 100 to 12 nm 75 to 200 mm 100 - >200 wph

Emerging markets are taking advantage of the performance and productivity of our mature products

Our holistic lithography portfolio underpins our success ASML

Lithography scanner with advanced control capability



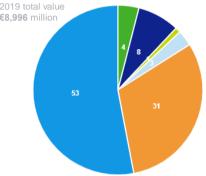
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2019 €11.8B - A record year



ASML sales grew by 8% despite an overall decline in our industry reflecting bedwyr Humphreys the increasing importance of lithography in the semiconductor industry

Net system sales breakdown (% system sales) 2019 total value



Sales of lithography systems (units)



Compelling market drivers

Major innovation drivers such as *artificial intelligence*, *5G*, *high-performance computing*, *autonomous driving and big data* are enabling new end-user applications.

These applications require a larger number of highperformance *Logic chips*, fueling demand for leading-edge nodes.

€2.0bn

€11.8bn

R&D

Revenue

Investing in the future

Our focus is on bringing our current EUV technology to the maturity level of our DUV systems and developing the next-generation EUV technology: High-NA.

In addition to EUV developments, we continue to invest in our DUV technology and our Metrology & Inspection product portfolio.

Open Innovation from design to manufacturing



ASML